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PROGRAMME

TOPIC 3  Poster Session 2, Wednesday, 18:30-21:30  Yellow Hall

W-3-28  A High Performance Organic Nonvolatile Memory Based on High-K Dielectric HfO₂ Charge-Trapping Layer
Wenchao Xu¹, Xubing Lu² and J. M. Liu³¹,²
¹South China Normal University, ²Nanjing University

W-3-29  Photo-responsive field-effect transistors (FETs) using organic tetracene/MoS₂ hybrid
Hyeon Jung Park¹, Jun Young Kim¹, Min Su Kim¹, Jeongyong Kim²,³ and Jinsoo Joo¹
¹Korea University, Seoul, ²Institute for Basic Science, ³Sungkyunkwan University

W-3-30  Flexible Solution-processed Ambipolar Thin-film Transistors Based on Polymer/Octadecyl-phosphonic Acid Treated Indium Oxide Hybrid Structure with Balanced Hole and Electron Mobilities
Sheng Sun, Linfeng Lan, Yuzhi Li, Zhenhui Chen and Junbiao Peng
South China University of Technology

W-3-31  Ambipolar performance of organic field-effect transistors based on single crystals
Liqun Liu¹, Jian Deng¹, Yan Wang¹ and Yuguang Ma¹,²
¹Jilin University, ²South China University of Technology

W-3-32  Control of Major Carriers in an Ambipolar Semiconductor Polymer by Self-Assembled Monolayers on the Dielectric Surface
Masahiro Nakano, Itaru Osaka and Kazuo Takimiya
Emergent Molecular Function Research Group, RIKEN Center for Emergent Mater Science

W-3-33  Two-Dimensional π-Expanded Quinoidal Oligothiophenes as n-Type Semiconductors for High-Performance Organic Thin-Film Transistors
Cheng Zhang, Yaping Zhang, Chong-an Di and Xiaozhang Zhu
Institute of Chemistry, Chinese Academy of Sciences

W-3-34  Interface characteristics of organic rubrene/MoS₂ hybrids and nanooptoelectronic devices
Cheol-Joon Park¹, Hyeon Jung Park¹, Yong-Jun Lee², Jinsoo Joo¹ and Jeongyong Kim²
¹Korea University, Seoul, ²Sungkyunkwan University